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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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2SC4262

Silicon NPN Epitaxial



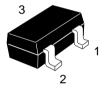
ADE-208-1100A (Z) 2nd. Edition Mar. 2001

Application

UHF / VHF Local oscillator

Outline

CMPAK



- 1. Emitter
- 2. Base
- 3. Collector

Note: Marking is "IP-".

2SC4262

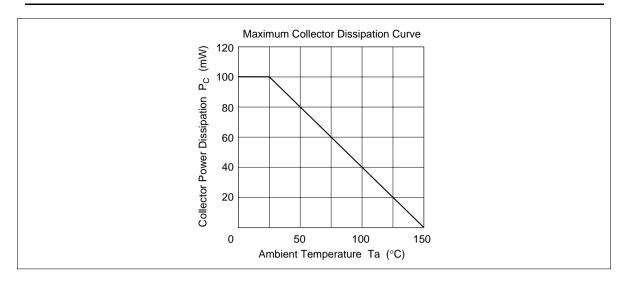
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	20	V	
Collector to emitter voltage	V_{CEO}	15	V	
Emitter to base voltage	V_{EBO}	3	V	
Collector current	I _c	50	mA	
Collector power dissipation	P _c	100	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

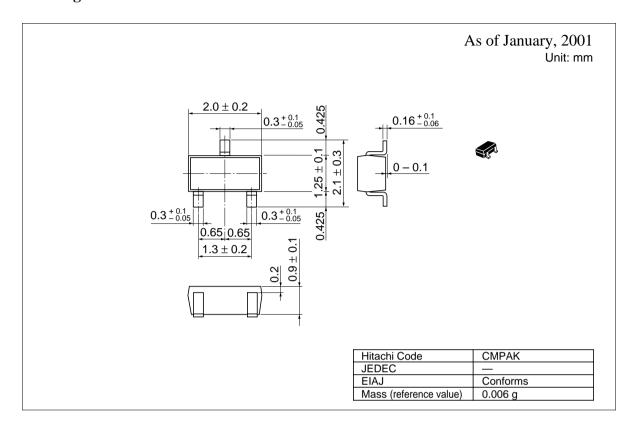
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	_	_	V	$I_{c} = 10 \ \mu\text{A}, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	15	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} =$
Collector cutoff current	I _{CBO}	_	_	0.5	μA	V _{CB} = 15 V, I _E = 0
Emitter cutoff current	I _{EBO}	_	_	1.0	μΑ	$V_{EB} = 3 \text{ V}, I_{C} = 0$
Collector to emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	_	_	0.5	V	$I_{\rm C}$ = 20 mA, $I_{\rm B}$ = 4 mA
DC current transfer ratio	h _{FE}	50	_	200		$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$
Collector output capacitance	Cob	_	_	1.0	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{MHz}$
Gain bandwidth product	f _T	1.4	2.9	_	GHz	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$

See characteristic curves of 2SC3793.



Package Dimensions



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Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica http://semiconductor.hitachi.com/ http://www.hitachi-eu.com/hel/ecg Europe Asia http://sicapac.hitachi-asia.com Japan http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Germany

Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Fax: <1>(408) 433-0223 Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <886>-(2)-2718-3666 Tel: <44> (1628) 585000 Fax: <44> (1628) 585160

Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00, Singapore 049318 Tel: <65>-538-6533/538-8577 Fax: <65>-538-6933/538-3877 URL: http://www.hitachi.com.sg

Hitachi Asia Ltd. (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road, Hung-Kuo Building, Taipei (105), Taiwan

Fax: <886>-(2)-2718-8180 Telex: 23222 HAS-TP URL: http://www.hitachi.com.tw Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon, Hong Kong

Tel: <852>-(2)-735-9218 Fax: <852>-(2)-730-0281 URL: http://www.hitachi.com.hk

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